

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A method comprising the steps of:  
forming an insulating film comprising silicon oxide by using an organic silane gas and a halogen containing gas over a glass substrate by plasma CVD,  
wherein the insulating film includes halogen and carbon and a concentration of the halogen in the insulating film is  $5 \times 10^{20} \text{ cm}^{-3}$  or less and a concentration of the carbon in the insulating film is  $5 \times 10^{19} \text{ cm}^{-3}$  or less.
2. (Previously Presented) A method according to claim 1, wherein the halogen is chlorine.
3. (Previously Presented) A method according to claim 1, wherein the insulating film includes carbon at a concentration of  $1 \times 10^{18} \text{ cm}^{-3}$  or less which is detected by the secondary ion mass spectroscopy.
4. (Original) A method according to claim 1, wherein said insulating film is a gate insulating film.
5. (Original) A method according to claim 1, wherein the insulating film is an insulating film in a thin film transistor.
6. (Original) A method according to claim 1, wherein the insulating film covers an even surface over the glass substrate.

7. (Original) A method according to claim 1, wherein the insulating film includes halogen at a concentration of  $1 \times 10^{17} \text{ cm}^{-3}$  or more.

8. (Currently Amended) A method of producing a semiconductor device, said method comprising the steps of:

forming a crystalline semiconductor island over a glass substrate; and

forming an insulating film including silicon oxide by using an organic silane gas and a halogen containing gas by plasma CVD to cover the crystalline semiconductor island,

wherein the insulating film includes halogen and carbon and a concentration of the halogen in the insulating film is  $5 \times 10^{20} \text{ cm}^{-3}$  or less and a concentration of the carbon in the insulating film is  $5 \times 10^{19} \text{ cm}^{-3}$  or less.

9. (Original) A method according to claim 8, wherein the concentrations of halogen and carbon are detected by secondary ion mass spectroscopy.

10. (Previously Presented) A method according to claim 8, wherein the halogen is chlorine.

11. (Canceled)

12. (Original) A method according to claim 8, wherein the insulating film includes halogen at a concentration of  $1 \times 10^{17} \text{ cm}^{-3}$  or more.

13. (Currently Amended) A method of fabricating a thin film transistor, said method comprising the steps of:

forming a crystalline semiconductor island over a glass substrate:

forming an insulating film comprising silicon oxide by using an organic silane gas and a halogen containing gas by plasma CVD over the crystalline semiconductor island; and

forming a conductive film including at least one of aluminum, titanium, and titanium nitride, said conductive film being formed on the insulating film,

wherein the insulating film includes halogen and carbon and a concentration of the halogen in the insulating film is  $5 \times 10^{20} \text{ cm}^{-3}$  or less and a concentration of the carbon in the insulating film is  $5 \times 10^{19} \text{ cm}^{-3}$  or less.

14. (Previously Presented) A method according to claim 13, wherein the halogen is chlorine.

15. (Canceled)

16. (Previously Presented) A method according to claim 13, wherein the insulating film includes halogen at a concentration of  $1 \times 10^{17} \text{ cm}^{-3}$  or more.

17. (Currently Amended) A method of fabricating a thin film transistor, said method comprising the steps of:

forming a crystalline semiconductor island over a glass substrate;

forming a gate insulating film including silicon oxide by using an organic silane gas and a halogen containing gas by plasma CVD on the crystalline semiconductor island; and

forming a gate electrode on the insulating film,

wherein the gate insulating film includes halogen and carbon and a concentration of the halogen in the gate insulating film is  $5 \times 10^{20} \text{ cm}^{-3}$  or less and a concentration of the carbon in the gate insulating film is  $5 \times 10^{19} \text{ cm}^{-3}$  or less.

18. (Previously Presented) A method according to claim 17, wherein the halogen is chlorine.

19. (Canceled)

20. (Original) A method according to claim 17, wherein the gate insulating film includes halogen at a concentration of  $1 \times 10^{17} \text{ cm}^{-3}$  or more.

21. (Previously Presented) A method according to claim 1, wherein the halogen is fluorine.

22. (Previously Presented) A method according to claim 8, wherein the halogen is fluorine.

23. (Previously Presented) A method according to claim 13, wherein the halogen is fluorine.

24. (Previously Presented) A method according to claim 17, wherein the halogen is fluorine.

25-36. (Canceled)

37. (Previously Presented) A method according to claim 1 wherein the concentrations of halogen and carbon are detected by the secondary ion mass spectroscopy.

38. (Previously Presented) A method according to claim 13, wherein the concentrations of halogen and carbon are detected by secondary ion mass spectroscopy.

39. (Previously Presented) A method according to claim 17, wherein the concentrations of halogen and carbon are detected by secondary ion mass spectroscopy.

40. (Previously Presented) A method according to claim 25, wherein the concentrations of halogen and carbon are detected by secondary ion mass spectroscopy.

41-42. (Canceled)